2SB649(A)

Rev.E Mar.-2016

蓝箭电子 BLUE ROCKET ELECTRONICS

DATA SHEET

/ Descriptions

WR0459I ṂṂ Ł SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

лъ 5VG99<+D, Ӣ ´

Complementary pair with 2SD669(A).

/ Applications

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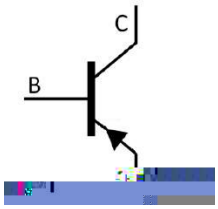
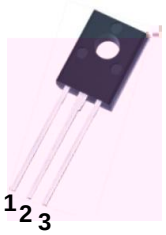
Low frequency power amplifier.

/ Equivalent Circuit



/ Pinning

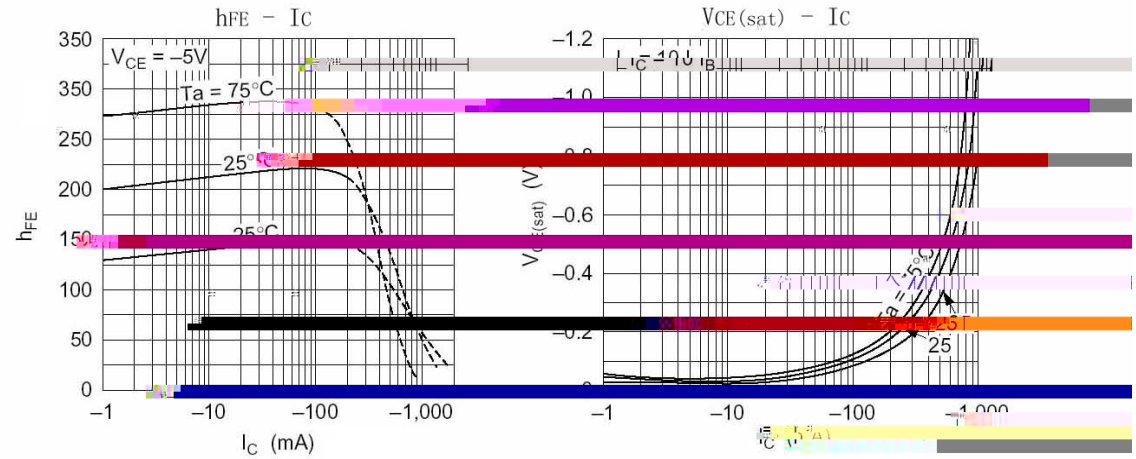


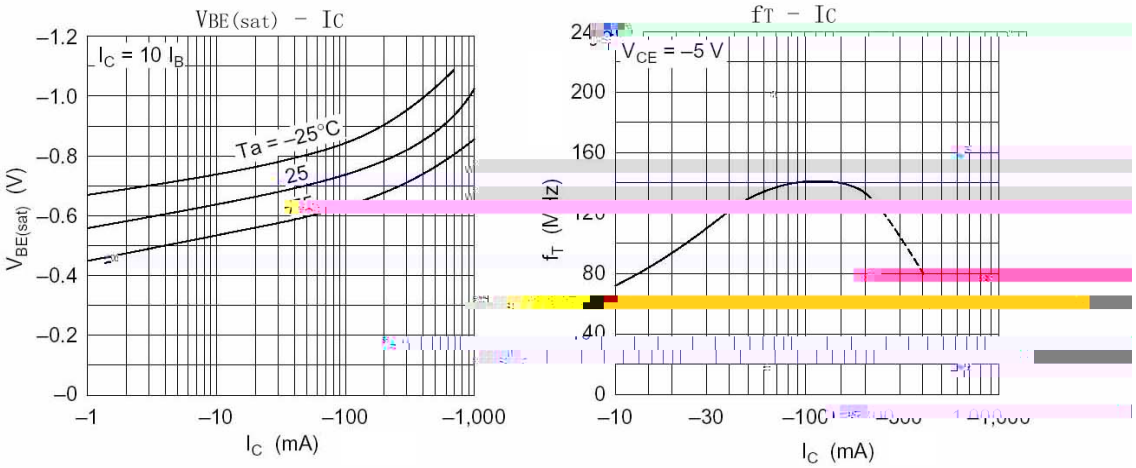
PIN1 χ Emitter PIN 2 χ Collector PIN 3 χ Base

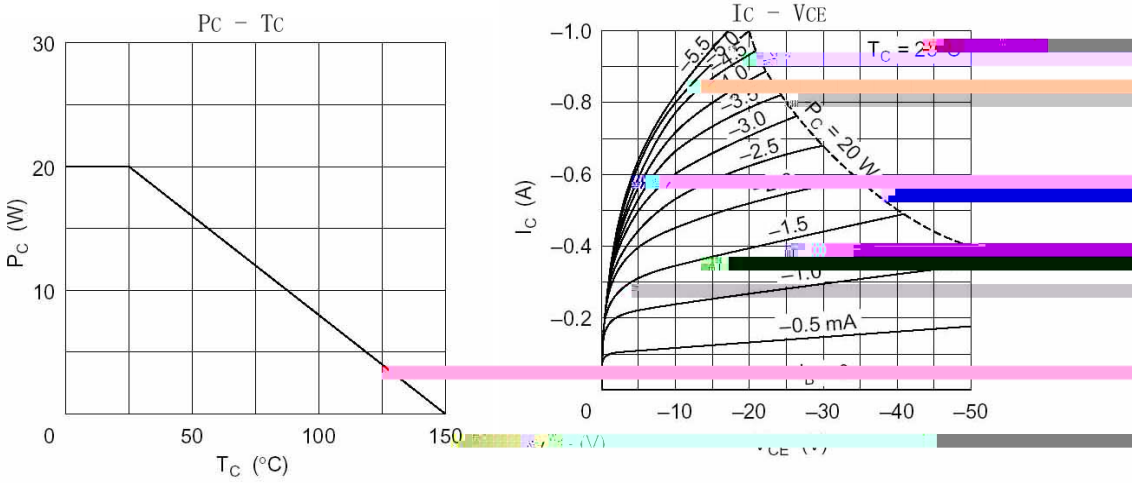
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

/ Electrical Characteristic Curve

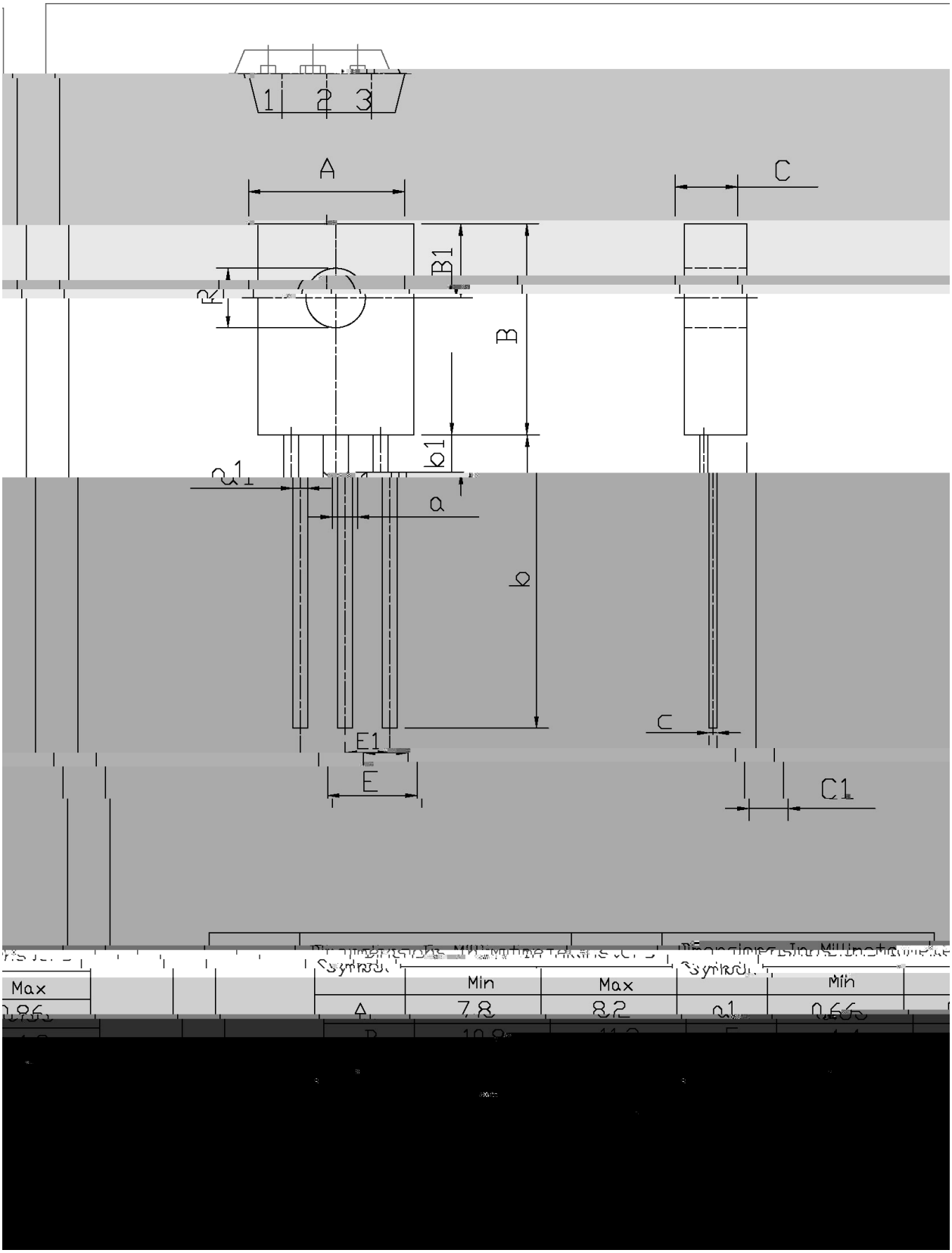






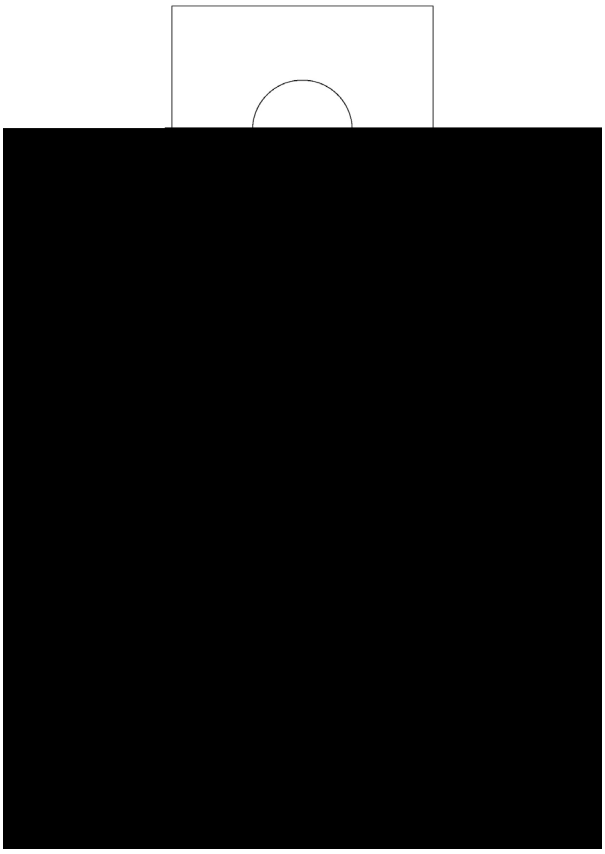
/ Package Dimensions

TO-126T 单位：mm



Symbol	Min	Max	Symbol	Min	Max
A	7.8	8.2	a1	0.66	
B	10.8	11.2	E	1.1	

/ Marking Instructions



ِ ˝ χ	
EU χ	ѭ ϗ И Ґ
E97< χ	ѭ ϳ N Ґ
E=	ѭ k IH ‘ 6 Ґ
---- χ	ѭ ł ғ ń N Ґ ı ₴ ł ғ ń N Ψ ק
Note:	
BR:	Company Code
B649 :	Product Type.
B:	h_{FE} Classifications Symbol
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)

ب ˝ χ

1 Ĺ ♬ □ ẙ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ë □ ẙ 255 ° 5 ɬ ı `H ڑ `Y ʎ ʁ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ﻉ ẙ ʁ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

5 • **Ủ 2** **õ** ʙ **I** 255 °